

WHAT IS CLAIMED IS:

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P1  
1. A driving method for a solid-state image sensing device having a plurality of sensor portions being disposed two-dimensionally in a horizontal and a vertical directions, and a vertical charge transfer portion being disposed between said plurality of sensor portions and being provided with transfer electrodes of a plurality of systems disposed along its disposed direction, comprising the steps of:

selectively applying high level driving pulses to said transfer electrodes of said plurality of systems in respective sectional periods in a vertical transfer period; and

transferring the signal charges read out from said plurality of sensor portions in the vertical direction;

wherein a sectional period in a vertical transfer period, in which the number of systems of said transfer electrodes to be applied with high level driving pulses becomes minimum is set longer than that of the other sectional periods.

2. A driving method for a solid-state image sensing device according to claim 1, having said transfer electrodes of said plurality of systems being composed of four systems and the vertical transfer period being divided into eight sections from t1 through t8, wherein

sectional periods  $t_2$ ,  $t_4$ ,  $t_6$  and  $t_8$ , those in which the number of systems of said transfer electrodes to be applied with the high level driving pulses becomes two, are set longer than the sectional periods  $t_1$ ,  $t_3$ ,  $t_5$  and  $t_7$ , those in which the number of systems of said transfer electrodes to be applied with said high level driving pulses becomes three.

3. A driving method for a charge transfer device having a charge transfer portion being formed of transfer electrodes of a plurality of systems disposed in the charge transfer direction, comprising the steps of:

selectively applying a high level driving pulse to said transfer electrodes of said plurality of systems in respective sectional periods in a transfer period; and

transferring signal charges in a charge transfer portion;

wherein a sectional period in said transfer period, in which the number of systems of said transfer electrodes to be applied with high level driving pulses becomes minimum are set longer than that of the other sectional periods.

4. A driving method for charge transfer devices according to claim 3, having said transfer electrodes of said plurality of systems being composed of four systems and the vertical transfer period being divided into eight

sections from t1 through t8, wherein the sectional periods t2, t4, t6 and t8, those in which the number of systems of said transfer electrodes to be applied with the high level driving pulses becomes two, are set longer than the sectional periods t1, t3, t5 and t7, those in which the number of systems of said transfer electrodes to be applied with high level driving pulses becomes three.

5. A charge transfer device having a charge transfer portion being formed of transfer electrodes of a plurality of systems disposed in the charge transfer direction;

wherein high level driving pulses are applied to said transfer electrodes of said plurality of systems in respective sectional periods in a charge transfer period;

signal charges in a charge transfer portion are transferred; and

a sectional period in a charge transfer period, in which the number of systems of said transfer electrodes to be applied with high level driving pulses becomes minimum is set longer than that of the other sectional periods.